Quad 2-Input Data Selectors/Multiplexers

High-Performance Silicon-Gate CMOS

The MC74HC157A is identical in pinout to the LS157. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device routes 2 nibbles (A or B) to a single port (Y) as determined by the Select input. The data is presented at the outputs in noninverted form. A high level on the Output Enable input sets all four Y outputs to a low level.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 82 FETs or 20.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

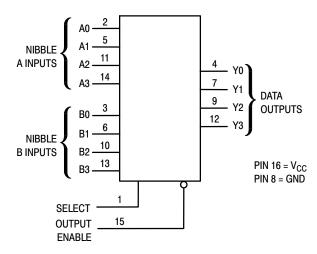


Figure 1. Logic Diagram



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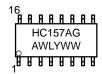


SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

PIN ASSIGNMENT

SELECT [1 ●	16	v _{cc}
A0 [2	15	OUTPUT ENABLE
В0 [3	14	_ A3
Y0 [4	13] B3
A1 [5	12] Y3
B1 [6	11	A2
Y1 [7	10] B2
GND [8	9	Y2

MARKING DIAGRAMS





SOIC-16

G or ■

A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week

(Note: Microdot may be in either location)

= Pb-Free Package

FUNCTION TABLE

Inp		
Output Enable	Select	Outputs Y0 – Y3
Н	Х	L
L	L	A0-A3
L	Н	B0-B3

X = don't care A0-A3, B0-B3 = the levels of the respective Data-Word Inputs.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: –7 mW/°C from 65° to 125°C TSSOP Package: –6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V _{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+125	°C
t _r , t _f	(Figure 1) V _{CC}	= 2.0 V = 4.5 V = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	Guaranteed Limit		
Symbol	Parameter	Test Conditions	v _{cc} v	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High–Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High–Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{split} V_{in} = V_{IH} & I_{out} \leq 2.4 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{\text{in}} = V_{\text{IL}} & I_{\text{out}} \leq 2.4 \text{ mA} \\ I_{\text{out}} \leq 6.0 \text{ mA} \\ I_{\text{out}} \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
l _{OZ}	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±0.5	±5.0	±10	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \ pF$, Input $t_r = t_f = 6.0 \ ns$)

			Gu			
Symbol	Parameter	v _{cc}	–55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 4)	2.0 3.0 4.5 6.0	105 65 21 18	130 85 26 22	160 115 32 27	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Select to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 70 22 19	140 90 28 24	165 115 33 28	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 4)	2.0 3.0 4.5 6.0	100 60 20 17	125 80 25 21	150 110 30 26	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	33	рF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

PIN DESCRIPTIONS

INPUTS

A0, A1, A2, A3 (Pins 2, 5, 11, 14)

Nibble A inputs. The data present on these pins is transferred to the outputs when the Select input is at a low level and the Output Enable input is at a low level. The data is presented to the outputs in noninverted form.

B0, B1, B2, B3 (Pins 3, 6, 10, 13)

Nibble B inputs. The data present on these pins is transferred to the outputs when the Select input is at a high level and the Output Enable input is at a low level. The data is presented to the outputs in noninverted form.

OUTPUTS

Y0, Y1, Y2, Y3 (Pins 4, 7, 9, 12)

Data outputs. The selected input Nibble is presented at these outputs when the Output Enable input is at a low level.

The data present on these pins is in its noninverted form. For the Output Enable input at a high level, the outputs are at a low level.

CONTROL INPUTS Select (Pin 1)

Nibble select. This input determines the data word to be transferred to the outputs. A low level on this input selects the A inputs and a high level selects the B inputs.

Output Enable (Pin 15)

Output Enable input. A low level on this input allows the selected input data to be presented at the outputs. A high level on this input sets all outputs to a low level.

SWITCHING WAVEFORMS

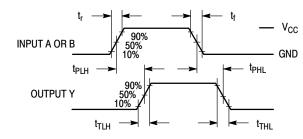


Figure 2. HC157A

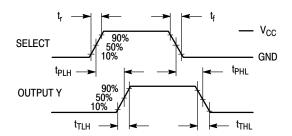


Figure 3. Y versus Selected, Noninverted

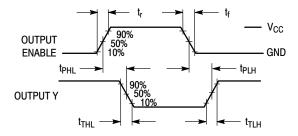
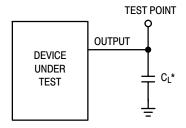


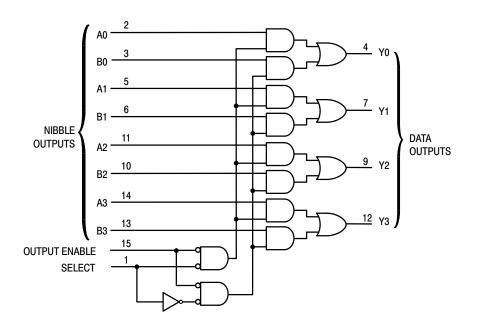
Figure 4. HC157A



*Includes all probe and jig capacitance

Figure 5. Test Circuit

EXPANDED LOGIC DIAGRAM



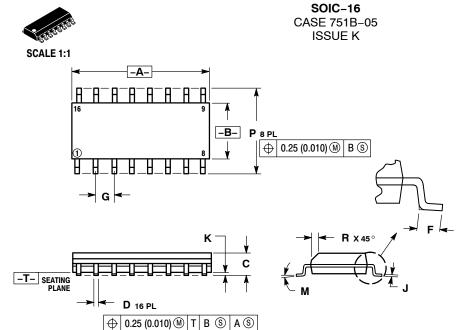
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC157ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC157ADR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74HC157ADTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLV74HC157ADR2G*	SOIC-16 (Pb-Free)	2500 / Tape & Reel
NLV74HC157ADTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
7	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR EMITTER COLLECTOR COLLECTOR COLLECTOR	2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE NO CONNECTION ANODE CATHODE CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION	STYLE 3: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. 15. 16.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3 COLLECTOR, #3 COLLECTOR, #4 BASE, #4 EMITTER, #4 COLLECTOR, #4	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. 15.	COLLECTOR, DYE COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 EMITTER, #4 BASE, #3 EMITTER, #3 BASE, #2 EMITTER, #2 BASE, #1 EMITTER, #1	SOLDERING FOOTPRINT SX 6.40 6.40	
STYLE 5: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	DRAIN, DYE #1 DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #2 SOURCE, #3 GATE, #2 SOURCE, #1 SOURCE, #1	3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	STYLE 7: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14. 15.	SOURCE N-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT SOURCE N-CH		16 0.£	16X 1.12	1.27 PITCH

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DESCRIPTION:	SOIC-16		PAGE 1 OF 1

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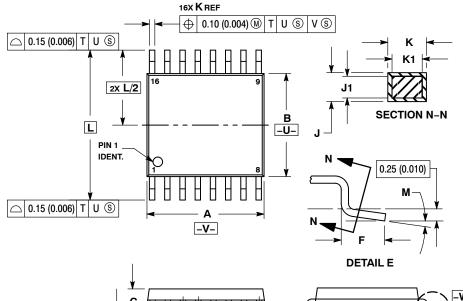
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



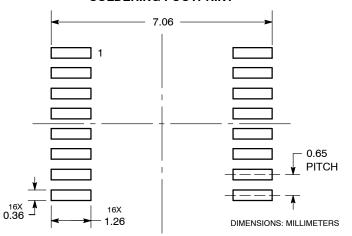
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
H	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Ы	6.40		0.252 BSC		
М	0 °	8°	0 °	8 °	

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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